SiA911ADJ vs. SiA911DJ

Description: **Dual P-Channel, 20-V (D-S) MOSFET**
Package: **PowerPAK® SC-70**
Pin Out: **Identical**

Part Number Replacements: SiA911ADJ-T1-GE3 replaces SiA911DJ-T1-GE3

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
PARAMETER		**SYMBOL**	**SiA911ADJ**	**SiA911DJ**	**UNIT**
Drain-Source Voltage		V_{DS}	- 20	- 20	V
Gate-Source Voltage		V_{GS}	± 8	± 8	
Continuous Drain Current	T_A = 25 °C	I_D	- 3.2	- 3.6	A
	T_A = 70 °C		- 2.6	- 2.9	
Pulsed Drain Current		I_{DM}	- 8	- 8	
Continuous Source Current (MOSFET Diode Conduction)		I_S	- 1.5	- 1.6	
Maximum Power Dissipation	T_A = 25 °C	P_D	1.8	1.9	W
	T_A = 70 °C		1.1	1.2	
Operating Junction and Storage Temperature Range		T_J and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	70	65	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
			SiA911ADJ			**SiA911DJ**			
PARAMETER		**SYMBOL**	**MIN.**	**TYP.**	**MAX.**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static									
Gate-Threshold Voltage		$V_{GS(th)}$	- 0.4		- 1	- 0.4		- 1	V
Gate-Body Leakage		I_{GSS}			± 100			± 100	nA
Zero Gate Voltage Drain Current (25 °C)		I_{DSS}			- 1			- 1	µA
On-State Drain Current	V_{GS} = - 4.5 V	$I_{D(on)}$	- 8			- 8			A
Drain-Source On-Resistance	V_{GS} = - 4.5 V	$R_{DS(on)}$		0.096	0.116		0.078	0.094	Ω
	V_{GS} = - 2.5 V			0.125	0.155		0.109	0.131	
	V_{GS} = - 1.8 V			0.165	0.205		0.153	0.185	
Forward Transconductance		g_{fs}		7			7		S
Diode Forward Voltage		V_{SD}		- 0.8	- 1.2		- 0.85	- 1.2	V
Dynamic									
Total Gate Charge		Q_g		4.9	7.4		4.9	7.4	nC
Gate-Source Charge		Q_{gs}		0.75			0.75		
Gate-Drain Charge		Q_{gd}		1.2			1.2		
Gate Resistance		R_g		6			8		Ω

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.